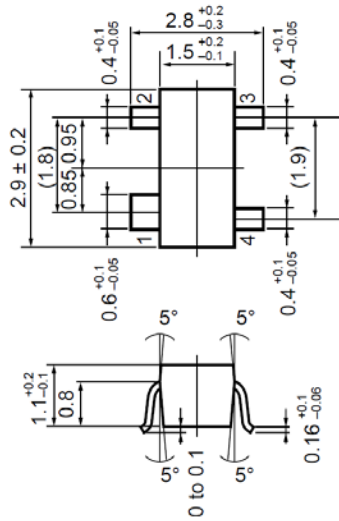


2SC5455A NPN Epitaxial Silicon Transistor mini mold for TK-2312 & TK-3312

PACKAGE DIMENSIONS (in mm)



PIN CONNECTIONS

- 1: Collector
- 2: Emitter
- 3: Base
- 4: Emitter

EPCOM syscom

1630 Paisano Dr.

El Paso. Tx 79901.

Ph (915)533-5119

www.epcom.net

SYSCOM

Ave 20 de Noviembre No. 805 Col. Centro

Chihuahua, Chih. 31000

Tel 052 (614) 415 – 2525

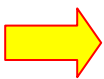
www.syscom.mx

TK-2312/2317

PARTS LIST

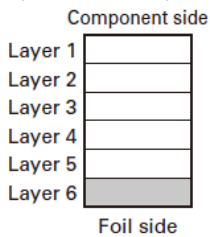
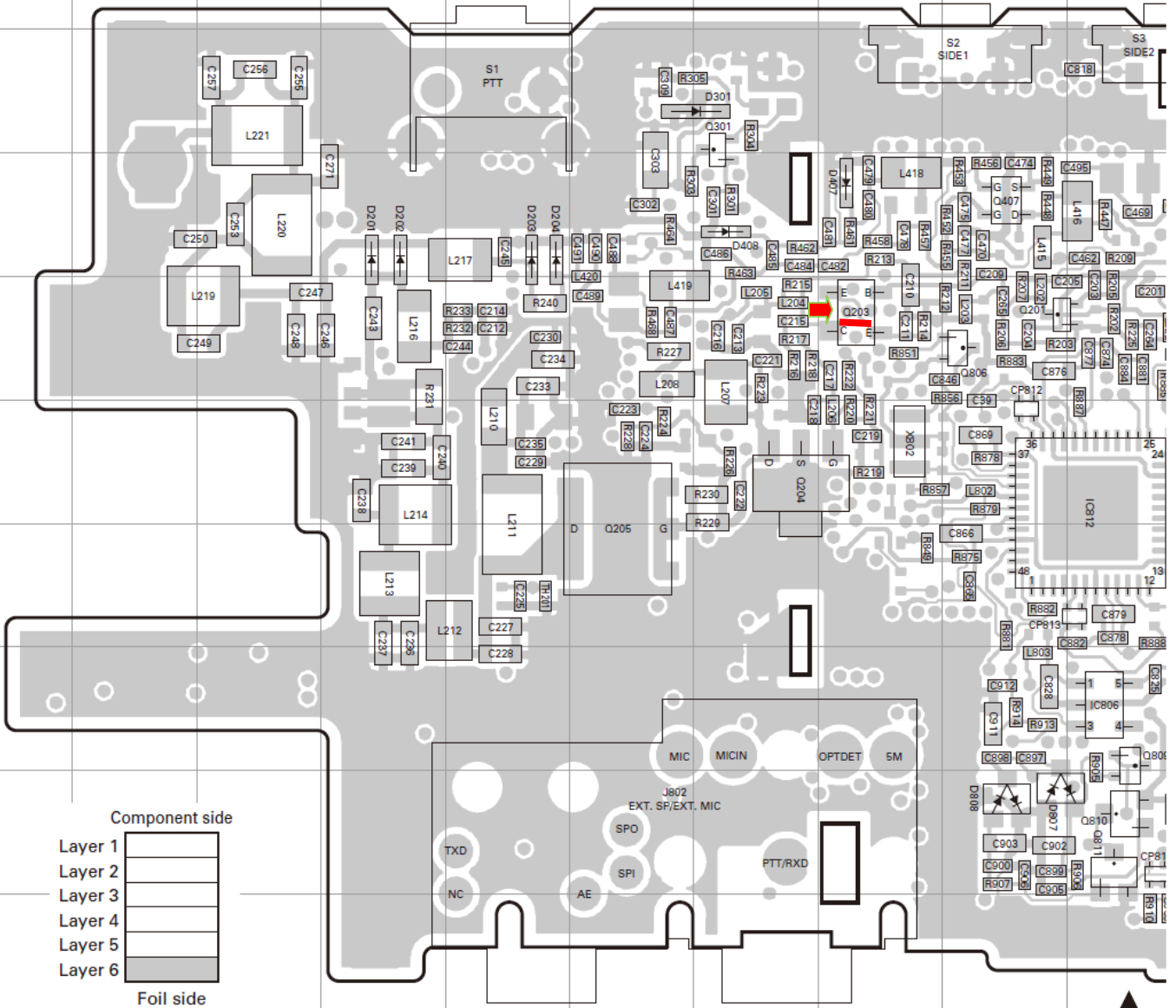
TX-RX UNIT (X57-7880-20)

Ref. No.	Address	New parts	Parts No.	Description	Desti-nation	Ref. No.	Address	New parts	Parts No.	Description	Desti-nation
IC401			NJM2591V	BI-POLAR IC							
IC402		*	NJU7108	MOS-IC							
IC801			XC6209B502PR	MOS-IC							
IC802			XC6209B502MR	MOS-IC							
IC803			XC6209B502PR	MOS-IC							
IC804			XC6209B332MR	MOS-IC							
IC805			XC61CN4502MR	MOS-IC							
IC806			XC6209B332MR	MOS-IC							
IC807			XC6120N302N1	MOS-IC							
IC808			NJM2904RB1-ZB	BI-POLAR IC							
IC810		*	EX25512ATA00A	ROM IC							
IC811			HA1630D03MM	MOS-IC							
IC812		*	CD686A03	MOS-IC							
IC815			TA7368FG	MOS-IC							
IC817			TC75S51FE(F)	MOS-IC							
IC820		*	F363BEDFEKDLB	MICU							
IC821		*	NJU6434	MOS-IC							
Q2			2SC5636	TRANSISTOR							
Q3			KTC4075E(Y,GR)	TRANSISTOR							
Q4,5			MCH3914(7)-H	FET							
Q6			SSM6L05FU-F	FET							
Q7			SSM3J05FU-F	FET							
Q8,9			2SC5636	TRANSISTOR							
Q11			SSM3J05FU-F	FET							
Q12			2SK1830F	FET							
Q201			2SC5636	TRANSISTOR							
Q203			2SC5455-A	TRANSISTOR							
Q204			RD01MUS1-T113	FET							
Q205			RD07MUS2BT112	FET							
Q301			RT1N140U-T111	TRANSISTOR							



TK-2312/2317 PC BOARD

TX-RX UNIT (X57-7880-20) Foil side view (J79-0287-09)



Ref. No.	Address	Ref. No.	Address	Ref. No.	Address	Ref. No.	Address	Ref. No.	Address	Ref. No.	Address	Ref. No.	Address	Ref. No.	Address
IC1	9Q	IC806	8J	Q6	7L	Q301	3G	Q806	5I	D10	9L	D203	4E	D806	
IC2	8O	IC807	7P	Q7	8L	Q401	4N	Q809	8J	D12	10L	D204	4E	D807	
IC3	9R	IC808	4L	Q8	7M	Q403	5O	Q810	9J	D13	7L	D301	3G	D808	
IC401	5N	IC811	5K	Q9	7N	Q404	4N	Q811	9J	D14	9M	D401	3O	D809	
IC402	4O	IC812	6J	Q11	8P	Q405	6N	Q820	8R	D15	9M	D402	3O	D810	
IC801	6P	IC817	9K	Q12	9P	Q406	4M	Q821	8Q	D16	9N	D404	3L	D811	
IC802	7R	Q2	8P	Q201	5I	Q407	4I	D4	8M	D17	7M	D405	4K		
IC803	6Q	Q3	7M	Q203	5H	Q802	7P	D6	8M	D18	7M	D407	4H		
IC804	7Q	Q4	8L	Q204	6G	Q803	7O	D8	8M	D201	4D	D408	4G		
IC805	7R	Q5	8N	Q205	7F	Q804	7Q	D9	8M	D202	4D	D803	3R		

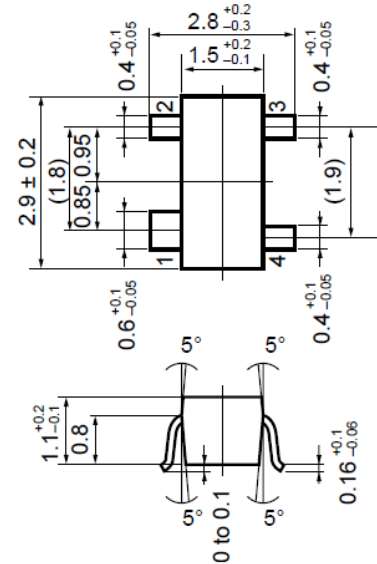
FEATURE

- Ideal for medium-output applications
- High gain, low noise
- Small reverse transfer capacitance
- Can operate at low voltage

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C)

PARAMETER	SYMBOL	RATING	UNIT
Collector to Base Voltage	V _{CB0}	9	V
Collector to Emitter Voltage	V _{CEO}	6	V
Emitter to Base Voltage	V _{EBO}	2	V
Collector Current	I _C	100	mA
Total Power Dissipation	P _T	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-65 to +150	°C

PACKAGE DIMENSIONS (in mm)



PIN CONNECTIONS

- 1: Collector
- 2: Emitter
- 3: Base
- 4: Emitter

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} = 5 V, I _E = 0			0.1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 1 V, I _C = 0			0.1	μA
DC Current Gain	h _{FE}	V _{CE} = 3 V, I _C = 30 mA ^{Note 1}	75		150	
Gain Bandwidth Product	f _T	V _{CE} = 3 V, I _C = 30 mA, f = 2 GHz		12.0		GHz
Reverse Transfer Capacitance	C _{re}	V _{CB} = 3 V, I _E = 0, f = 1 MHz ^{Note 2}		0.5	0.7	pF
Insertion Power Gain	S _{21e} ²	V _{CE} = 3 V, I _C = 30 mA, f = 2 GHz	8.0	10.0		dB
Noise Figure	NF	V _{CE} = 3 V, I _C = 7 mA, f = 2 GHz		1.5	2.5	dB

Notes 1. Pulse measurement P_w ≤ 350 μs, duty cycle ≤ 2 %

2. Collector to base capacitance measured by capacitance meter (automatic balance bridge method) when emitter pin is connected to the guard pin.